

NSS40500UW3T2G

40 V, 5.0 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

- This is a Pb-Free Device

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

| Rating | Symbol | Max | Unit |
|--------------------------------|-----------|----------------------------|------|
| Collector-Emitter Voltage | V_{CEO} | -40 | Vdc |
| Collector-Base Voltage | V_{CBO} | -40 | Vdc |
| Emitter-Base Voltage | V_{EBO} | -7.0 | Vdc |
| Collector Current - Continuous | I_C | -5.0 | Adc |
| Collector Current - Peak | I_{CM} | -6.0 | A |
| Electrostatic Discharge | ESD | HBM Class 3B MM Class C | |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|---------------------------------------|----------------|----------------------------|
| Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D (Note 1) | 875 7.0 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ (Note 1) | 143 | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D (Note 2) | 1.5 11.8 | W mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ (Note 2) | 85 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-Lead #1 | $R_{\theta JL}$ (Note 2) | 23 | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation (Single Pulse < 10 sec) | $P_{D\text{single}}$ (Notes 2 & 3) | 3.0 | W |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

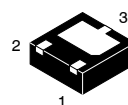
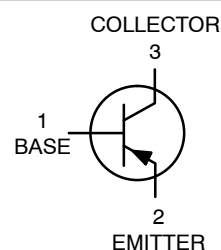
1. FR-4 @ 100 mm², 1 oz copper traces.
2. FR-4 @ 500 mm², 1 oz copper traces.
3. Thermal response.



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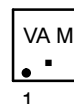
<http://onsemi.com>

-40 VOLTS
5.0 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 65 m Ω



WDFN3
CASE 506AU

MARKING DIAGRAM



- 1
- VA = Specific Device Code
 - M = Date Code
 - = Pb-Free Package

ORDERING INFORMATION

| Device | Package | Shipping† |
|----------------|--------------------|----------------------|
| NSS40500UW3T2G | WDFN3 (Pb-Free) | 3000/ Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSS40500UW3T2G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typical | Max | Unit |
|--|----------------------|------|---------|------|------------------|
| OFF CHARACTERISTICS | | | | | |
| Collector - Emitter Breakdown Voltage (I _C = -10 mA, I _B = 0) | V _{(BR)CEO} | -40 | - | - | Vdc |
| Collector - Base Breakdown Voltage (I _C = -0.1 mA, I _E = 0) | V _{(BR)CBO} | -40 | - | - | Vdc |
| Emitter - Base Breakdown Voltage (I _E = -0.1 mA, I _C = 0) | V _{(BR)EBO} | -7.0 | - | - | Vdc |
| Collector Cutoff Current (V _{CB} = -40 Vdc, I _E = 0) | I _{CBO} | - | - | -0.1 | μA _{dc} |
| Emitter Cutoff Current (V _{EB} = -7.0 Vdc) | I _{EBO} | - | - | -0.1 | μA _{dc} |

ON CHARACTERISTICS

| | | | | | |
|--|----------------------|---------------------------------|--|--|-----|
| DC Current Gain (Note 4) (I _C = -10 mA, V _{CE} = -2.0 V) (I _C = -500 mA, V _{CE} = -2.0 V) (I _C = -1.0 A, V _{CE} = -2.0 V) (I _C = -2.0 A, V _{CE} = -2.0 V) (I _C = -3.0 A, V _{CE} = -2.0 V) | h _{FE} | 250 250 220 180 150 | - - 300 250 200 | - - - - - | |
| Collector - Emitter Saturation Voltage (Note 4) (I _C = -0.1 A, I _B = -0.010 A) (Note 5) (I _C = -1.0 A, I _B = -0.100 A) (I _C = -1.0 A, I _B = -0.010 A) (I _C = -2.0 A, I _B = -0.020 A) (I _C = -3.0 A, I _B = -0.030 A) (I _C = -4.0 A, I _B = -0.400 A) | V _{CE(sat)} | - - - - - | -0.010 -0.065 -0.110 -0.190 -0.310 -0.215 | -0.015 -0.080 -0.130 -0.220 -0.340 -0.260 | V |
| Base - Emitter Saturation Voltage (Note 4) (I _C = -1.0 A, I _B = -0.01 A) | V _{BE(sat)} | - | -0.76 | -0.900 | V |
| Base - Emitter Turn-on Voltage (Note 4) (I _C = -2.0 A, V _{CE} = -3.0 V) | V _{BE(on)} | - | -0.80 | -0.900 | V |
| Cutoff Frequency (I _C = -100 mA, V _{CE} = -5.0 V, f = 100 MHz) | f _T | 100 | - | - | MHz |
| Input Capacitance (V _{EB} = -0.5 V, f = 1.0 MHz) | C _{ibo} | - | - | 475 | pF |
| Output Capacitance (V _{CB} = -3.0 V, f = 1.0 MHz) | C _{obo} | - | - | 150 | pF |

SWITCHING CHARACTERISTICS

| | | | | | |
|---|----------------|---|---|-----|----|
| Delay (V _{CC} = -30 V, I _C = 750 mA, I _{B1} = 15 mA) | t _d | - | - | 70 | ns |
| Rise (V _{CC} = -30 V, I _C = 750 mA, I _{B1} = 15 mA) | t _r | - | - | 150 | ns |
| Storage (V _{CC} = -30 V, I _C = 750 mA, I _{B1} = 15 mA) | t _s | - | - | 600 | ns |
| Fall (V _{CC} = -30 V, I _C = 750 mA, I _{B1} = 15 mA) | t _f | - | - | 160 | ns |

4. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%.
5. Guaranteed by design but not tested.

NSS40500UW3T2G

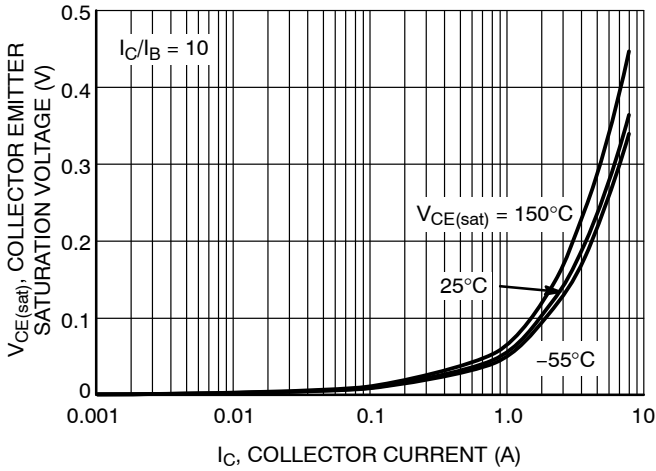


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

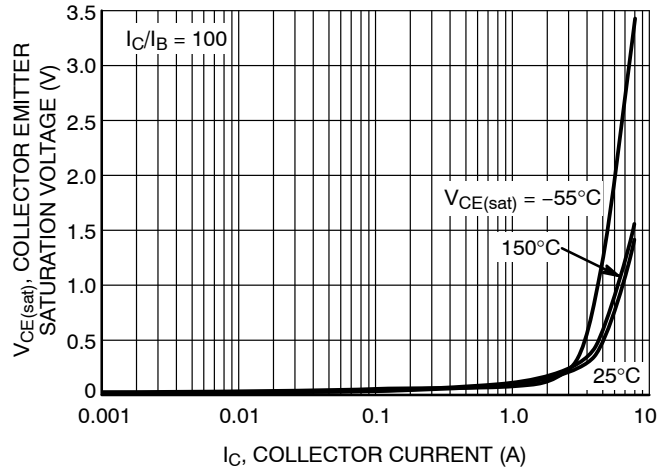


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

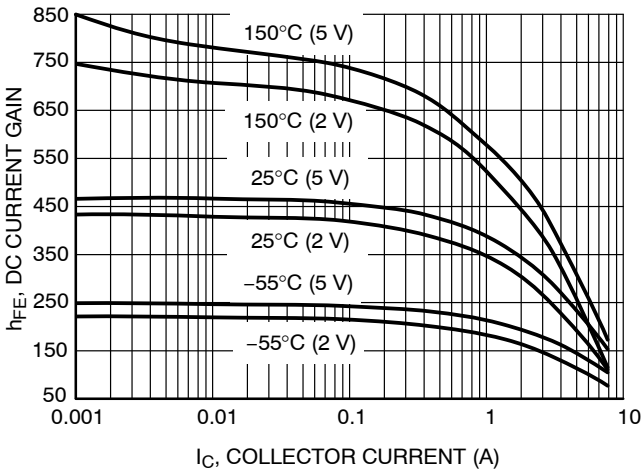


Figure 3. DC Current Gain vs. Collector Current

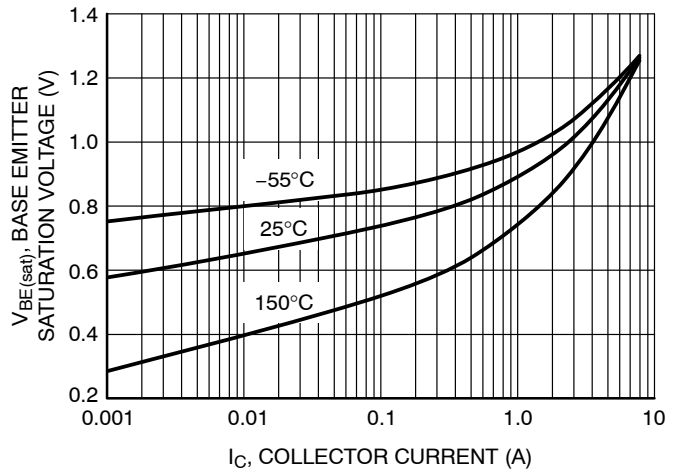


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

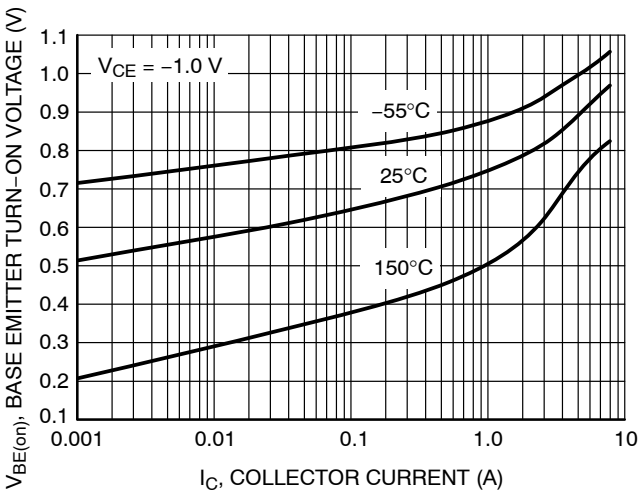


Figure 5. Base Emitter Turn-On Voltage vs. Collector Current

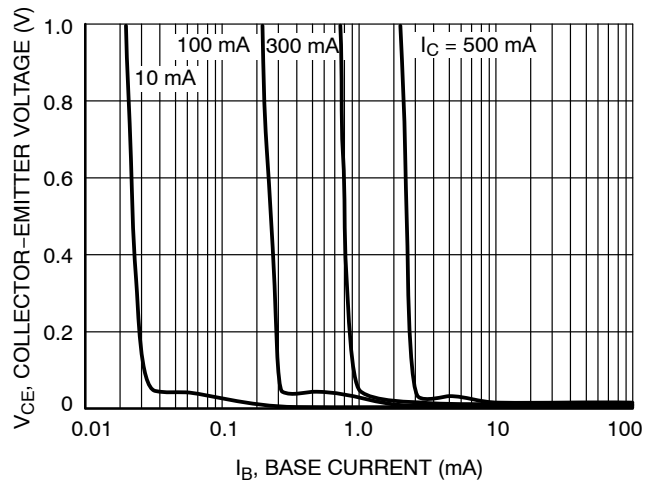


Figure 6. Saturation Region

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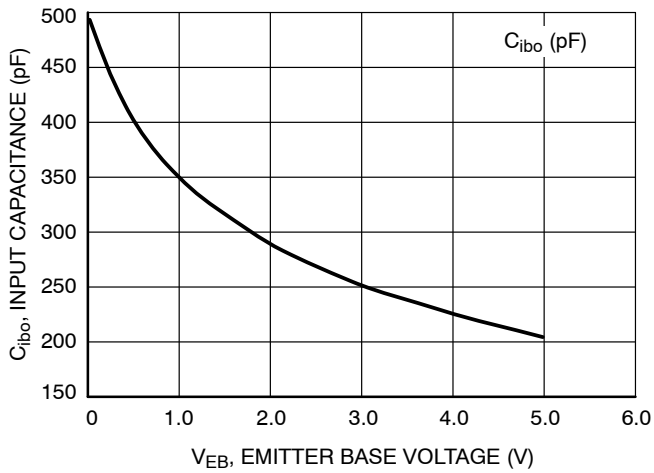


Figure 7. Input Capacitance

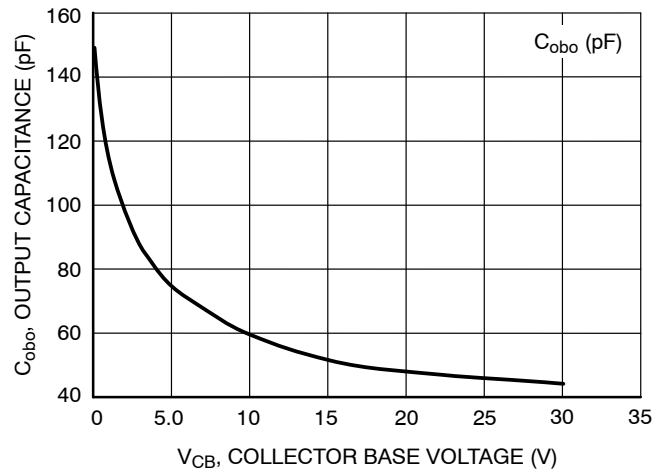


Figure 8. Output Capacitance

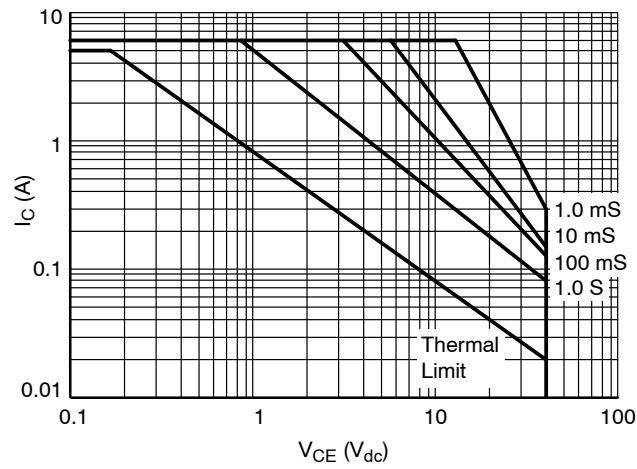


Figure 9. PNP Safe Operating Area

MECHANICAL CASE OUTLINE

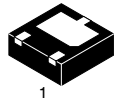
PACKAGE DIMENSIONS

ON Semiconductor®

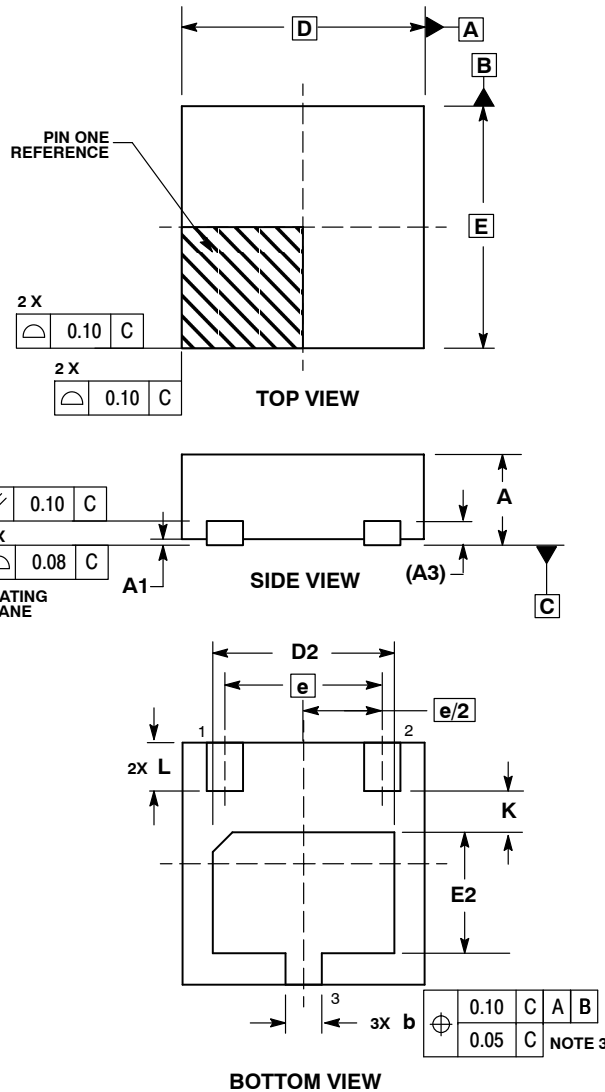


WDFN3 2x2, 1.3P CASE 506AU ISSUE A

DATE 18 AUG 2016



SCALE 4:1

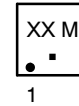


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 .
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|----------|------|--------|-----------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.70 | 0.75 | 0.80 | 0.028 | 0.030 | 0.031 |
| A1 | 0.00 | | 0.05 | 0.000 | | 0.002 |
| A3 | | 0.20 REF | | | 0.008 REF | |
| b | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 |
| D | | 2.00 BSC | | | 0.079 BSC | |
| D2 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| E | | 2.00 BSC | | | 0.079 BSC | |
| E2 | 0.90 | 1.00 | 1.10 | 0.035 | 0.039 | 0.043 |
| e | | 1.30 BSC | | | 0.051 BSC | |
| K | | 0.35 REF | | | 0.014 REF | |
| L | 0.35 | 0.40 | 0.45 | 0.014 | 0.016 | 0.018 |

GENERIC MARKING DIAGRAM*

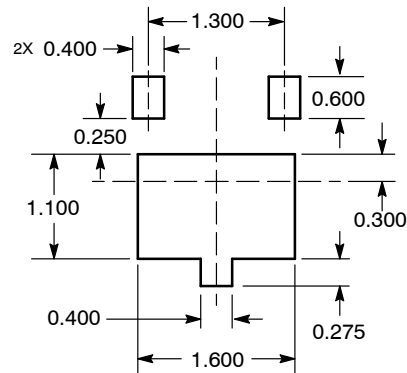


XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| | | |
|-------------------------|------------------------|--|
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